

**IN THE CLAIMS:**

Kindly cancel claims 1, 5, 6-10, and 17 without prejudice or disclaimer. Kindly amend claim 2 as follows. A detailed listing of all claims is as follows.

Claim 1 (Canceled).

Claim 2 (Currently Amended): A semiconductor laser device comprising:  
first and second laser units each having a ridge type structure and including a multilayer  
structure having an active layer, an n-type and p-type semiconductor layers sandwiching said  
active layer therebetween, a p-side electrode and an n-side electrode, wherein the ridge portions  
of said first and second laser units face each other at side surfaces of said ridge portion and the p-  
side electrode of the first laser unit is electrically connected to the n-side electrode of the second  
laser unit and the n-side electrode of the first laser unit is electrically connected to the p-side  
electrode of the second laser unit ~~The semiconductor laser device according to claim 1, further~~  
~~comprising:~~

a first connecting layer interconnecting said p-side electrode of the first laser unit and  
said n-side electrode of the second laser unit; and

a second connecting layer interconnecting between said p-side electrode of the second  
laser unit and said n-side electrode of the first laser unit.

Claim 3 (Original): The semiconductor laser device according to claim 2, wherein the  
first and second laser units are disposed in an opposing fashion with each other with an  
insulating layer interposed between the first and second laser units.

Claim 4 (Previously Presented): The semiconductor laser device according to claim 2, wherein at least one of said first and said second connecting layers has a Schottky barrier.

Claim 5-10 (Canceled).

Claim 11 (Previously Presented): The semiconductor laser device according to claim 3, wherein at least one of the connecting layers has a Schottky barrier.

Claim 12 (Previously Presented): The semiconductor laser device according to claim 2, wherein at least one of the first laser unit and the second laser unit has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

Claim 13 (Previously Presented): The semiconductor laser device according to claim 3, wherein at least one of the first laser unit and the second laser unit has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

Claim 14 (Previously Presented): The semiconductor laser device according to claim 2, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

Claim 15 (Previously Presented): The semiconductor laser device according to claim 3, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

Claim 16 (Previously Presented): The semiconductor laser device according to claim 4, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

Claim 17 (Canceled).